# Old Company Name in Catalogs and Other Documents

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April 1<sup>st</sup>, 2010 Renesas Electronics Corporation Issued by: Renesas Electronics Corporation (http://www.renesas.com) Send any inquiries to http://www.renesas.com/inquiry.

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Silicon PNP Epitaxial

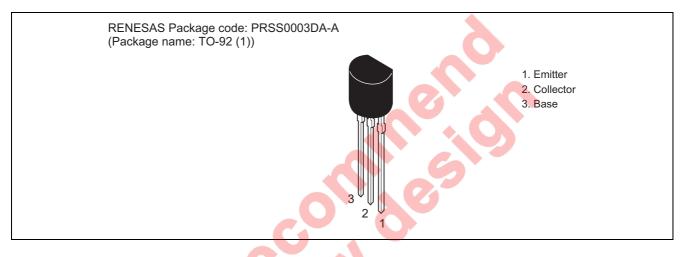
REJ03G0631-0200 (Previous ADE-208-1001) Rev.2.00 Aug.10.2005

# Application

### • Low frequency low noise amplifier

• Complementary pair with 2SC1775A

### Outline



# Absolute Maximum Ratings

|                              |                  | $(Ta = 25^{\circ}C)$ |      |  |
|------------------------------|------------------|----------------------|------|--|
| Item                         | Symbol           | Ratings              | Unit |  |
| Collector to base voltage    | V <sub>CBO</sub> | -120                 | V    |  |
| Collector to emitter voltage | V <sub>CEO</sub> | -120                 | V    |  |
| Emitter to base voltage      | V <sub>EBO</sub> | -5                   | V    |  |
| Collector current            | lc               | -50                  | mA   |  |
| Collector power dissipation  | Pc               | 300                  | mW   |  |
| Junction temperature         | Tj               | 150                  | °C   |  |
| Storage temperature          | Tstg             | -50 to +150          | °C   |  |



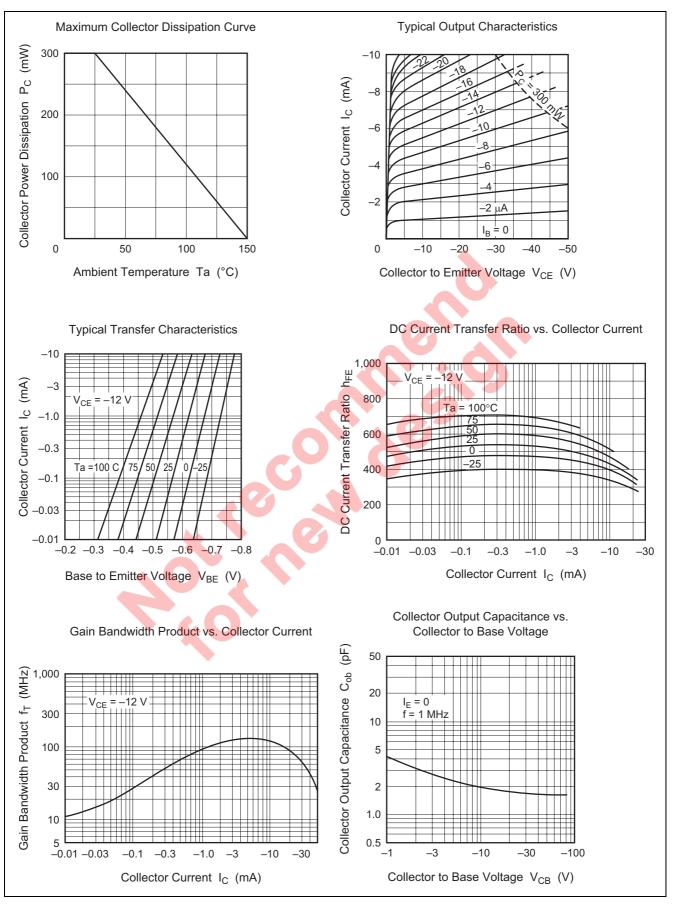
# **Electrical Characteristics**

| Note:         1.         The 2SA872A is grouped by h <sub>FE1</sub> as for           D         E           250 to 500         400 to 800   | ICEO     -12       30  | 20<br> | Гур<br>—<br>—<br>—<br>—<br>—<br>120<br>1.8<br>— | Max<br>                                 | Unit<br>V<br>μA<br>μA<br>V<br>V<br>MHz<br>PF<br>dB<br>dB | $\begin{tabular}{ c c c c } \hline Test conditions \\ \hline I_C = -1 mA, R_{BE} = \infty \\ \hline V_{CB} = -75 V, I_E = 0 \\ \hline V_{CE} = -100 V, I_E = 0 \\ \hline V_{CE} = -12 V, \\ \hline I_C = -2 mA \\ \hline V_{CE} = -12 V, \\ \hline I_C = -0.1 mA \\ \hline V_{CE} = -12 V, \\ \hline I_C = -2 mA \\ \hline I_C = -2 mA \\ \hline I_C = -2 mA \\ \hline I_C = -10 mA, \\ \hline I_B = -1 mA \\ \hline V_{CE} = -12 V, \\ \hline I_C = -2 mA \\ \hline V_{CE} = -12 V, \\ \hline I_C = -2 mA \\ \hline V_{CE} = -12 V, \\ \hline I_C = -2 mA \\ \hline V_{CE} = -25 V, I_E = 0, \\ \hline f = 1 MHz \\ \hline V_{CE} = -50 \mu A \\ \hline R_g = 50 k\Omega \\ \hline f = 1 \ \text{KHz} \\ \hline \end{tabular}$   |
|--|--|--------|---|---|--|---|
| Collector cutoff current       IcBo         DC current transfer ratio       hFE1*         Base to emitter voltage       VBE         Collector to emitter saturation voltage       VCE(sa         Gain bandwidth product       fT         Collector output capacitance       Cob         Noise figure       NF         Note:       1. The 2SA872A is grouped by hFE1 as fol         D       E         250 to 500       400 to 800           | 30        10        11     25       12     16       32     16       34        35        (sat)        -        0b        F        -        iollows. |        |   |   | μΑ<br>μΑ<br>V<br>V<br>MHz<br>pF<br>dB                    | $\begin{array}{l} V_{CB} = -75 \ V, \ I_E = 0 \\ V_{CE} = -100 \ V, \ I_E = 0 \\ V_{CE} = -12 \ V, \\ I_C = -2 \ mA \\ V_{CE} = -12 \ V, \\ I_C = -0.1 \ mA \\ V_{CE} = -12 \ V, \\ I_C = -2 \ mA \\ I_C = -2 \ mA \\ I_C = -10 \ mA, \\ I_B = -1 \ mA \\ V_{CE} = -12 \ V, \\ I_C = -2 \ mA \\ V_{CE} = -2 \ mA \\ I_C = -2 \ mA \\ V_{CE} = -2 \ mA \\ I_C = -2 \ mA \\ V_{CE} = -2 \ mA \\ I_C = -50 \ \muA \\ I_C = -5$ |
| DC current transfer ratio       hFE1*         DFFE2       Base to emitter voltage       VBE         Base to emitter voltage       VBE         Collector to emitter saturation voltage       VCE(se         Gain bandwidth product       fT         Collector output capacitance       Cob         Noise figure       NF         Note:       1. The 2SA872A is grouped by hFE1 as for         D       E         250 to 500       400 to 800 |  |        | — — — — — — — — — — — — — — — — — — —           | 0.5<br>800<br>                          | μA<br>V<br>V<br>MHz<br>pF<br>dB                          | $\begin{split} & V_{CE} = -100 \text{ V}, \text{ I}_{E} = 0 \\ & V_{CE} = -12 \text{ V}, \\ & I_{C} = -2 \text{ mA} \\ & V_{CE} = -12 \text{ V}, \\ & I_{C} = -0.1 \text{ mA} \\ & V_{CE} = -12 \text{ V}, \\ & I_{C} = -2 \text{ mA} \\ & I_{C} = -10 \text{ mA}, \\ & I_{B} = -1 \text{ mA} \\ & V_{CE} = -12 \text{ V}, \\ & I_{C} = -2 \text{ mA} \\ & V_{CE} = -12 \text{ V}, \\ & I_{C} = -2 \text{ mA} \\ & V_{CE} = -25 \text{ V}, \text{ I}_{E} = 0, \\ & f = 1 \text{ MHz} \\ & V_{CE} = -6 \text{ V}, \\ & I_{C} = -50 \text{ \muA} \\ & R_{g} = 50 \text{ k\Omega} \end{split}$   |
| hFE2         Base to emitter voltage       VBE         Collector to emitter saturation voltage       VCE(sa         Gain bandwidth product       fT         Collector output capacitance       Cob         Noise figure       NF         Note:       1. The 2SA872A is grouped by hFE1 as for         D       E         250 to 500       400 to 800  | E2 16<br>BE  | 0<br>  | —<br>—<br>—<br>120                              | 800<br><br>-0.75<br><br>-0.5<br><br>5.0 | V<br>V<br>MHz<br>pF<br>dB                                | $\begin{array}{l} V_{CE} = -12 \ V, \\ I_{C} = -2 \ mA \\ \hline \\ V_{CE} = -12 \ V, \\ I_{C} = -0.1 \ mA \\ \hline \\ V_{CE} = -12 \ V, \\ I_{C} = -2 \ mA \\ \hline \\ I_{C} = -2 \ mA \\ \hline \\ V_{CE} = -12 \ V, \\ I_{C} = -2 \ mA \\ \hline \\ V_{CE} = -12 \ V, \\ I_{C} = -2 \ mA \\ \hline \\ V_{CB} = -25 \ V, \ I_{E} = 0, \\ f = 1 \ MHz \\ \hline \\ V_{CE} = -6 \ V, \\ I_{C} = -50 \ \muA \\ \hline \\ R_{g} = 50 \ k\Omega \end{array}$   |
| hFE2         Base to emitter voltage       VBE         Collector to emitter saturation voltage       VCE(sa         Gain bandwidth product       fT         Collector output capacitance       Cob         Noise figure       NF         Note:       1. The 2SA872A is grouped by hFE1 as for         D       E         250 to 500       400 to 800  | E2 16<br>BE  | - 1    |   | <br>-0.75<br>0.5<br><br>5.0             | V<br>MHz<br>pF<br>dB                                     | $\begin{split} I_{C} &= -2 \text{ mA} \\ V_{CE} &= -12 \text{ V}, \\ I_{C} &= -0.1 \text{ mA} \\ V_{CE} &= -12 \text{ V}, \\ I_{C} &= -2 \text{ mA} \\ I_{C} &= -2 \text{ mA} \\ I_{C} &= -1 \text{ mA} \\ V_{CE} &= -12 \text{ V}, \\ I_{C} &= -2 \text{ mA} \\ V_{CB} &= -25 \text{ V}, I_{E} &= 0, \\ f &= 1 \text{ MHz} \\ V_{CE} &= -6 \text{ V}, \\ I_{C} &= -50 \text{ \muA} \\ R_{g} &= 50 \text{ k\Omega} \end{split}$   |
| Base to emitter voltage       VBE         Collector to emitter saturation voltage       VCE(set         Gain bandwidth product       fT         Collector output capacitance       Cob         Noise figure       NF         Note:       1. The 2SA872A is grouped by hFE1 as for         D       E         250 to 500       400 to 800  | se –<br>(sat) –<br>ob –<br>F –<br>follows.   | - 1    | —<br>—<br>120                                   | -0.75<br>-0.5<br><br>5.0                | V<br>MHz<br>pF<br>dB                                     | $\begin{array}{l} V_{CE} = -12 \ V, \\ I_{C} = -0.1 \ mA \\ V_{CE} = -12 \ V, \\ I_{C} = -2 \ mA \\ I_{C} = -2 \ mA \\ I_{C} = -10 \ mA, \\ I_{B} = -1 \ mA \\ V_{CE} = -12 \ V, \\ I_{C} = -2 \ mA \\ V_{CE} = -25 \ V, \ I_{E} = 0, \\ f = 1 \ MHz \\ V_{CE} = -6 \ V, \\ I_{C} = -50 \ \muA \\ R_{g} = 50 \ k\Omega \end{array}$   |
| Base to emitter voltage       VBE         Collector to emitter saturation voltage       VCE(set         Gain bandwidth product       fT         Collector output capacitance       Cob         Noise figure       NF         Note:       1. The 2SA872A is grouped by hFE1 as fot         D       E         250 to 500       400 to 800  | se –<br>(sat) –<br>ob –<br>F –<br>follows.   | - 1    | —<br>—<br>120                                   | -0.75<br>-0.5<br><br>5.0                | V<br>MHz<br>pF<br>dB                                     | $\begin{split} & I_{C} = -0.1 \text{ mA} \\ & V_{CE} = -12 \text{ V}, \\ & I_{C} = -2 \text{ mA} \\ & I_{C} = -10 \text{ mA}, \\ & I_{B} = -1 \text{ mA} \\ & V_{CE} = -12 \text{ V}, \\ & I_{C} = -2 \text{ mA} \\ & V_{CB} = -25 \text{ V}, \\ & I_{C} = -25 \text{ V}, \\ & I_{E} = 0, \\ & f = 1 \text{ MHz} \\ & V_{CE} = -6 \text{ V}, \\ & I_{C} = -50 \text{ \muA} \\ & R_{g} = 50 \text{ k\Omega} \end{split}$   |
| Collector to emitter saturation voltage       V <sub>CE(sate</sub> Gain bandwidth product       fT         Collector output capacitance       Cob         Noise figure       NF         Note:       1. The 2SA872A is grouped by h <sub>FE1</sub> as for         D       E         250 to 500       400 to 800   | (sat) —<br>- —<br>bb —<br>F —<br>-<br>follows.   |        |   | -0.5<br><br>5.0                         | V<br>MHz<br>pF<br>dB                                     | $\begin{array}{l} V_{CE} = -12 \ V, \\ I_{C} = -2 \ mA \\ \hline I_{C} = -10 \ mA, \\ I_{B} = -1 \ mA \\ \hline V_{CE} = -12 \ V, \\ I_{C} = -2 \ mA \\ \hline V_{CB} = -25 \ V, \ I_{E} = 0, \\ f = 1 \ MHz \\ \hline V_{CE} = -6 \ V, \\ I_{C} = -50 \ \muA \\ \hline R_{g} = 50 \ k\Omega \end{array} \right _{f} = 10 \ Hz$   |
| Collector to emitter saturation voltage       V <sub>CE(sate</sub> Gain bandwidth product       fT         Collector output capacitance       Cob         Noise figure       NF         Note:       1. The 2SA872A is grouped by h <sub>FE1</sub> as for         D       E         250 to 500       400 to 800   | (sat) —<br>- —<br>bb —<br>F —<br>-<br>follows.   |        |   | -0.5<br><br>5.0                         | V<br>MHz<br>pF<br>dB                                     | $\begin{split} I_{C} &= -2 \text{ mA} \\ I_{C} &= -10 \text{ mA}, \\ I_{B} &= -1 \text{ mA} \\ V_{CE} &= -12 \text{ V}, \\ I_{C} &= -2 \text{ mA} \\ V_{CB} &= -25 \text{ V}, I_{E} &= 0, \\ f &= 1 \text{ MHz} \\ V_{CE} &= -6 \text{ V}, \\ I_{C} &= -50 \text{ \muA} \\ R_{g} &= 50 \text{ k}\Omega \end{split}$   |
| Gain bandwidth product       fT         Collector output capacitance       Cob         Noise figure       NF         Note:       1. The 2SA872A is grouped by hFE1 as for         D       E         250 to 500       400 to 800  | F –  |        |   |   | MHz<br>pF<br>dB  |   |
| Gain bandwidth product       fT         Collector output capacitance       Cob         Noise figure       NF         Note:       1. The 2SA872A is grouped by hFE1 as for         D       E         250 to 500       400 to 800  | F –  |        |   |   | MHz<br>pF<br>dB  |   |
| Collector output capacitance     Cob       Noise figure     NF       Note:     1. The 2SA872A is grouped by hFE1 as for       D     E       250 to 500     400 to 800  | F –  |        |   |   | pF<br>dB   | $ \begin{array}{l} V_{CE} = -12 \ V, \\ I_{C} = -2 \ mA \\ V_{CB} = -25 \ V, \ I_{E} = 0, \\ f = 1 \ MHz \\ V_{CE} = -6 \ V, \\ I_{C} = -50 \ \muA \\ R_{g} = 50 \ k\Omega \end{array} \left  \begin{array}{c} f = 10 \ Hz \\ f = 10 \ Hz \\ \end{array} \right  $  |
| Collector output capacitance     Cob       Noise figure     NF       Note:     1. The 2SA872A is grouped by hFE1 as for       D     E       250 to 500     400 to 800  | F –  |        |   |   | pF<br>dB   | $\label{eq:CB} \begin{array}{l} I_{C} = -2 \mbox{ mA} \\ V_{CB} = -25 \mbox{ V, } I_{E} = 0, \\ f = 1 \mbox{ MHz} \\ V_{CE} = -6 \mbox{ V, } f = 10 \mbox{ Hz} \\ I_{C} = -50 \mbox{ \muA} \\ R_{g} = 50 \mbox{ k}\Omega \end{array}$   |
| Noise figure         NF           Note:         1. The 2SA872A is grouped by h <sub>FE1</sub> as for           D         E           250 to 500         400 to 800   | F —  | -      | 1.8   |   | dB   | $ \begin{array}{c} V_{CB} = -25 \ V, \ I_E = 0, \\ f = 1 \ MHz \\ V_{CE} = -6 \ V, \ f = 10 \ Hz \\ I_C = -50 \ \mu A \\ R_g = 50 \ k\Omega \end{array} $   |
| Noise figure         NF           Note:         1. The 2SA872A is grouped by h <sub>FE1</sub> as for           D         E           250 to 500         400 to 800   | F —  | -      | 1.8   |   | dB   |   |
| Note:         1.         The 2SA872A is grouped by h <sub>FE1</sub> as for           D         E           250 to 500         400 to 800   | iollows.   | -      | -   |   |  | $V_{CE} = -6 V, f = 10 Hz$ $I_{C} = -50 \mu A$ $R_{g} = 50 k\Omega$   |
| Note:         1.         The 2SA872A is grouped by h <sub>FE1</sub> as for           D         E           250 to 500         400 to 800   | iollows.   | -      | -   |   |  | l <sub>c</sub> = –50 μA<br>R <sub>g</sub> = 50 kΩ   |
| D         E           250 to 500         400 to 800  |  | -      |   | 1.5                                     | dB   | R <sub>g</sub> = 50 kΩ  |
| D         E           250 to 500         400 to 800  |  | -      |   | 1.5                                     | dB   |   |
| D         E           250 to 500         400 to 800  |  |        | -   | 1.5                                     | dB   | f = 1 kHz   |
| D         E           250 to 500         400 to 800  |  | 0      |   |   |  | · ·   |
|  |  |        | 9.  |   |  |   |

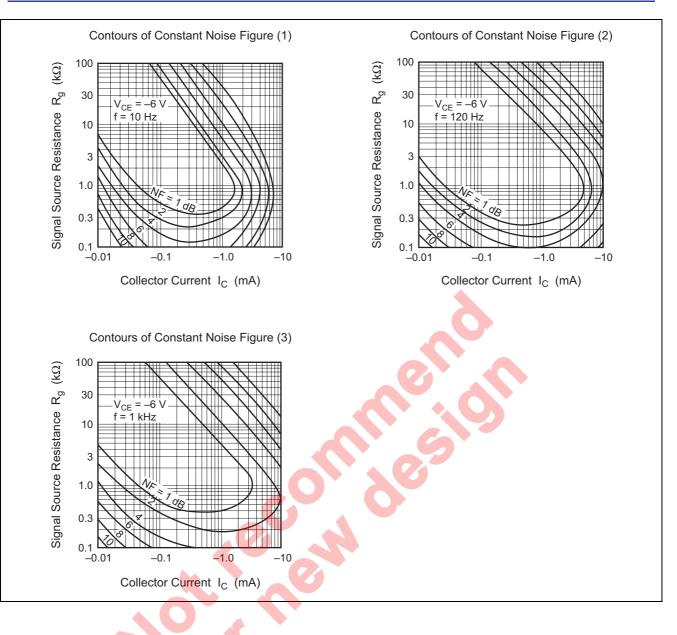
| D          | E          |
|------------|------------|
| 250 to 500 | 400 to 800 |



### **Main Characteristics**

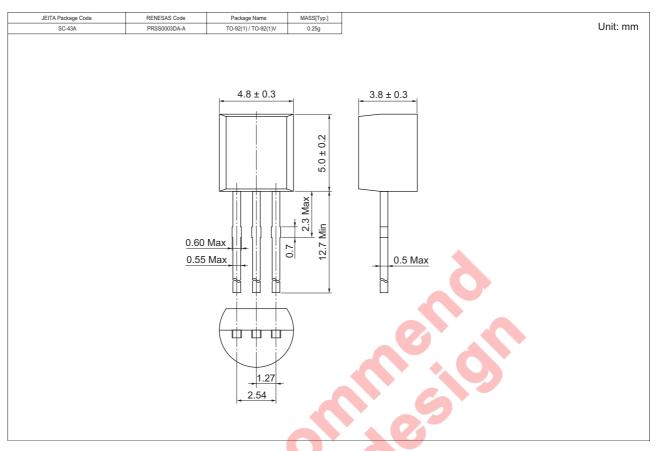








# **Package Dimensions**



# **Ordering Information**

| Part Name  | Quantity |   | Shipping Container     |
|------------|----------|---|------------------------|
| 2SA872ADTZ | 2500     | H | old Box, Radial Taping |
| 2SA872AETZ |          |   |                        |

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